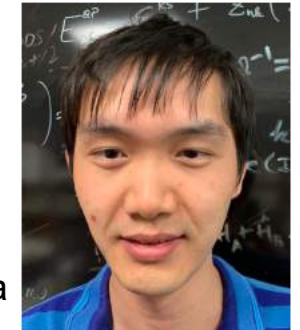


# Current Progress on Atomistic Modeling and Simulation of Coating Materials

Hai-Ping Cheng<sup>1</sup>

Jun Jiang<sup>1</sup>, Alec S. Mishkin<sup>1</sup>, Rui Zhang<sup>1</sup>,  
Kiran Prasai<sup>2</sup>, Riccardo Bassiri<sup>2</sup>, Martin M. Fejer<sup>2</sup>

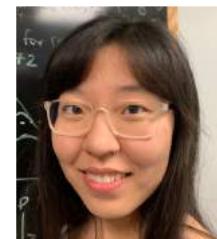


1. Department of Physics and the Quantum Theory Project, University of Florida
2. E. L. Ginzton Laboratory, Stanford University

Acknowledgement:



Alec  
Mishkin

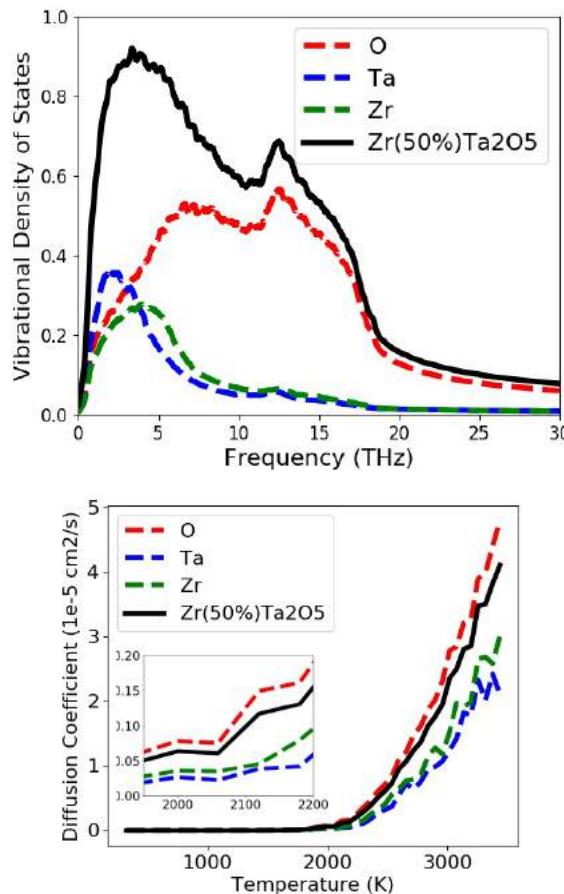


Rui  
Zhang

Jun  
Jiang

Zhang: Doped  $\text{Ta}_2\text{O}_5$

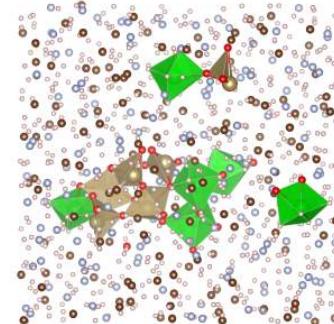
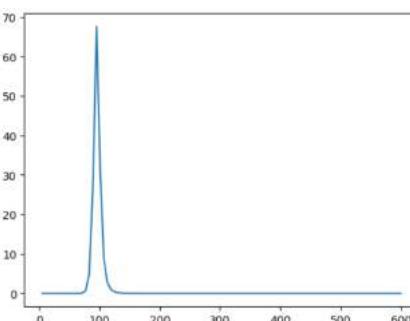
Vibrational DOS 300 K



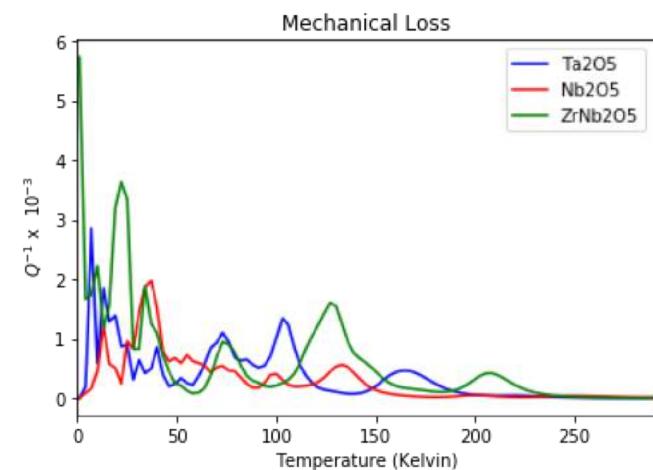
## Research Highlights

Jun Jiang

A thorough analysis of two-level system  
in 50% Zr-doped  $\text{Ta}_2\text{O}_5$  relating loss to atom  
displacement and much more!

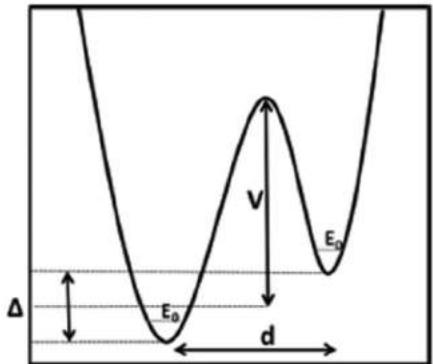


Mishkin: Comparison  
 $\text{Ta}_2\text{O}_5$ ,  $\text{Nb}_2\text{O}_5$ , and 14%  
Zr doped  $\text{Nb}_2\text{O}_5$



Zhang: Calculation of Raman  
spectra is on-going.....

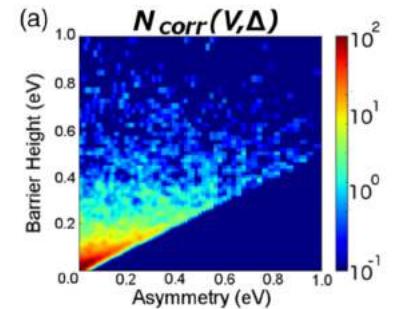
Key parameters for characterizing a TLS: barrier, asymmetry, tau, elastic modulus, coupling constant ...



$$Q^{-1}(T) = \frac{1}{3k_b T} \int \frac{\gamma^2 \Delta^2}{\epsilon E^2} \frac{\omega \tau}{1 + \omega^2 \tau^2} \operatorname{sech}^2 \left( \frac{E}{2k_b T} \right) n(V, \Delta, \gamma, \tau, \epsilon) dV d\Delta d\gamma d\tau d\epsilon$$

$$\Delta = \operatorname{abs}(E_1 - E_2) \quad E = \sqrt{\Delta^2 + \Delta_0^2}$$

$$V = \frac{V_1 + V_2}{2} = E_s - \frac{E_1 + E_2}{2} \quad \tau = \tau_0 \cosh^{-1} \left( \frac{\Delta}{2k_b T} \right) e^{\frac{V}{k_b T}}$$

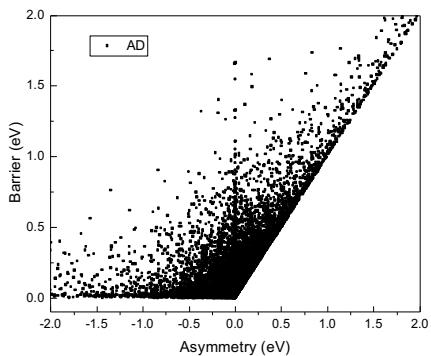


Chris R. Billman, et. al. PRB 95, 014109 (2017)

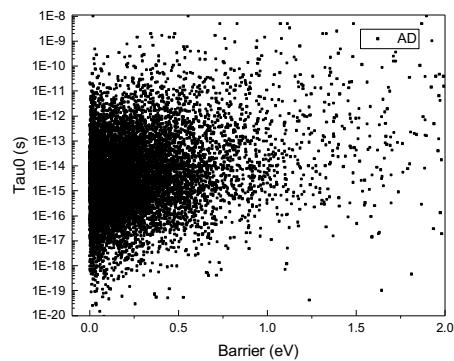
Starting samples: RMC generated to fit expt RDF & DFT relaxed  
~40 initial structure for as-deposit and ~40 for annealed (800k)

Parameters distribution ( barrier, asymmetry, tau...) for AD and AN 50% ZrO<sub>2</sub> doped Ta<sub>2</sub>O<sub>5</sub>

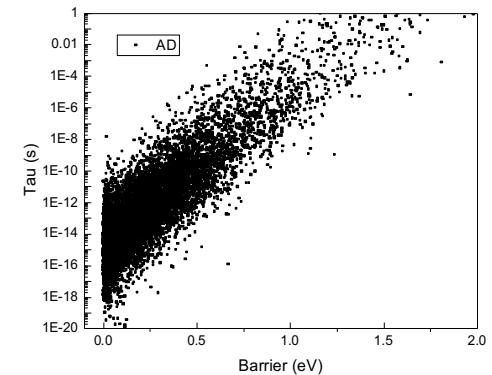
barrier vs asymmetry



barrier vs tau0



barrier vs tau

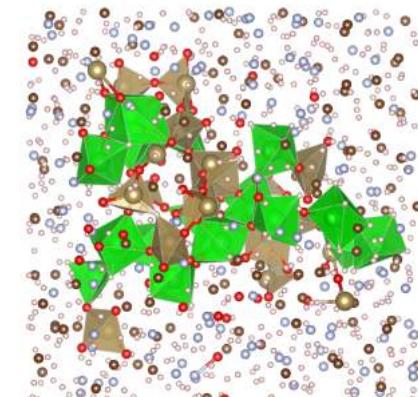
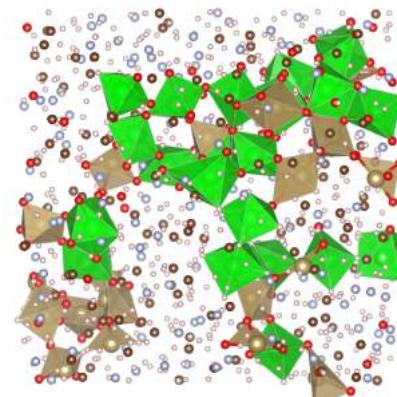
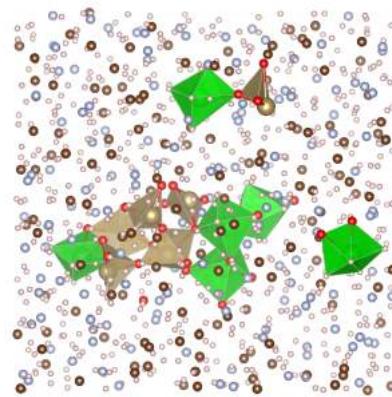
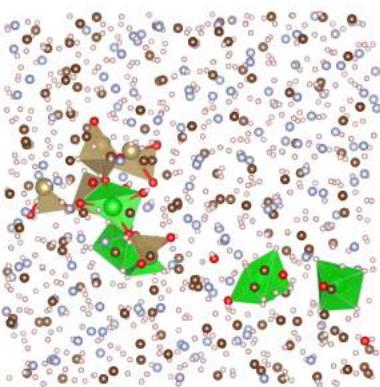
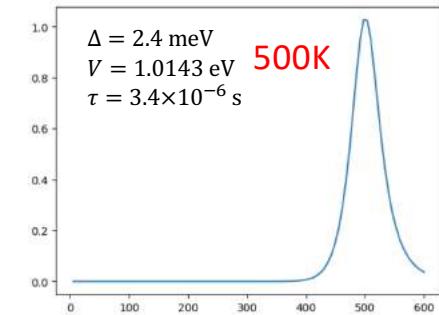
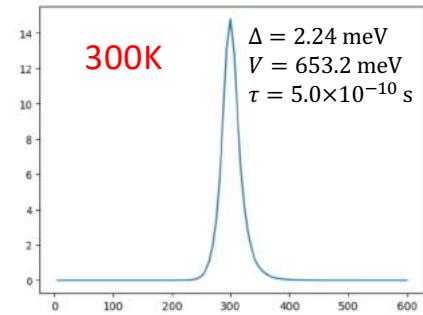
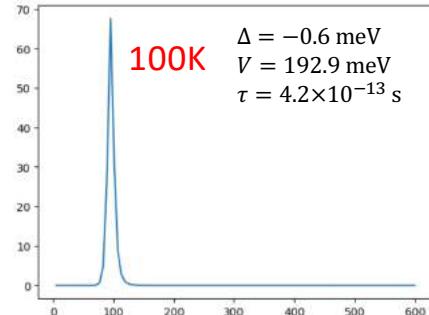
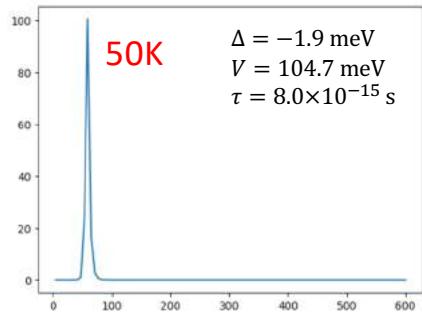


New modifications for a better description of TLS:

$$\Delta = \operatorname{abs}(E_1 - E_2) \rightarrow \Delta_1 \text{ and } \Delta_2$$

$$V = \frac{V_1 + V_2}{2} \rightarrow V_1 \text{ and } V_2$$

## Mechanical Loss from a single transition

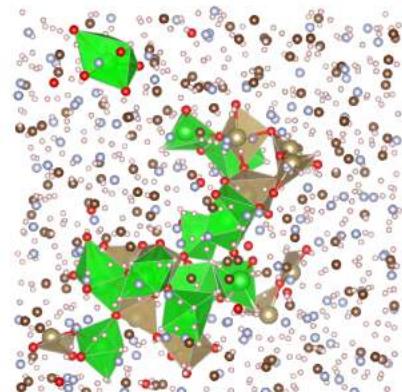
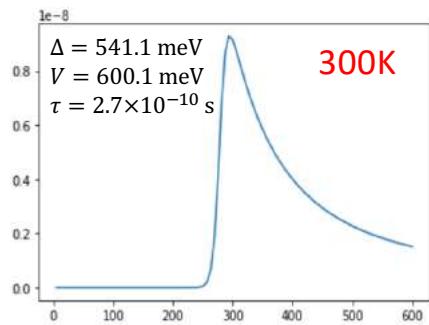


Chain

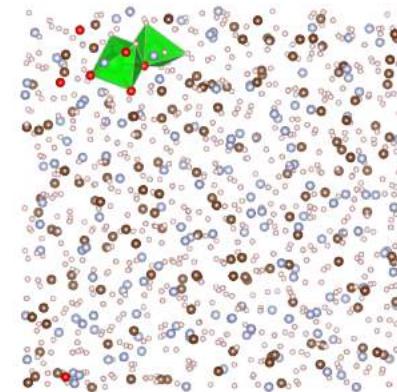
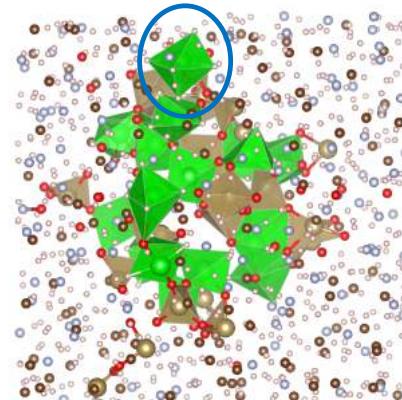
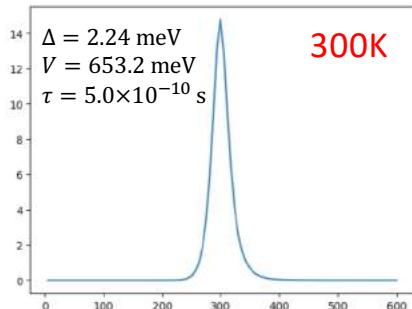
Cluster

Atoms moves more than 0.1 Å during transition. Green: Zr and Brown Ta; Oxygens are red dots

## Mechanical Loss from a single transition



Minimum1 -> Saddle

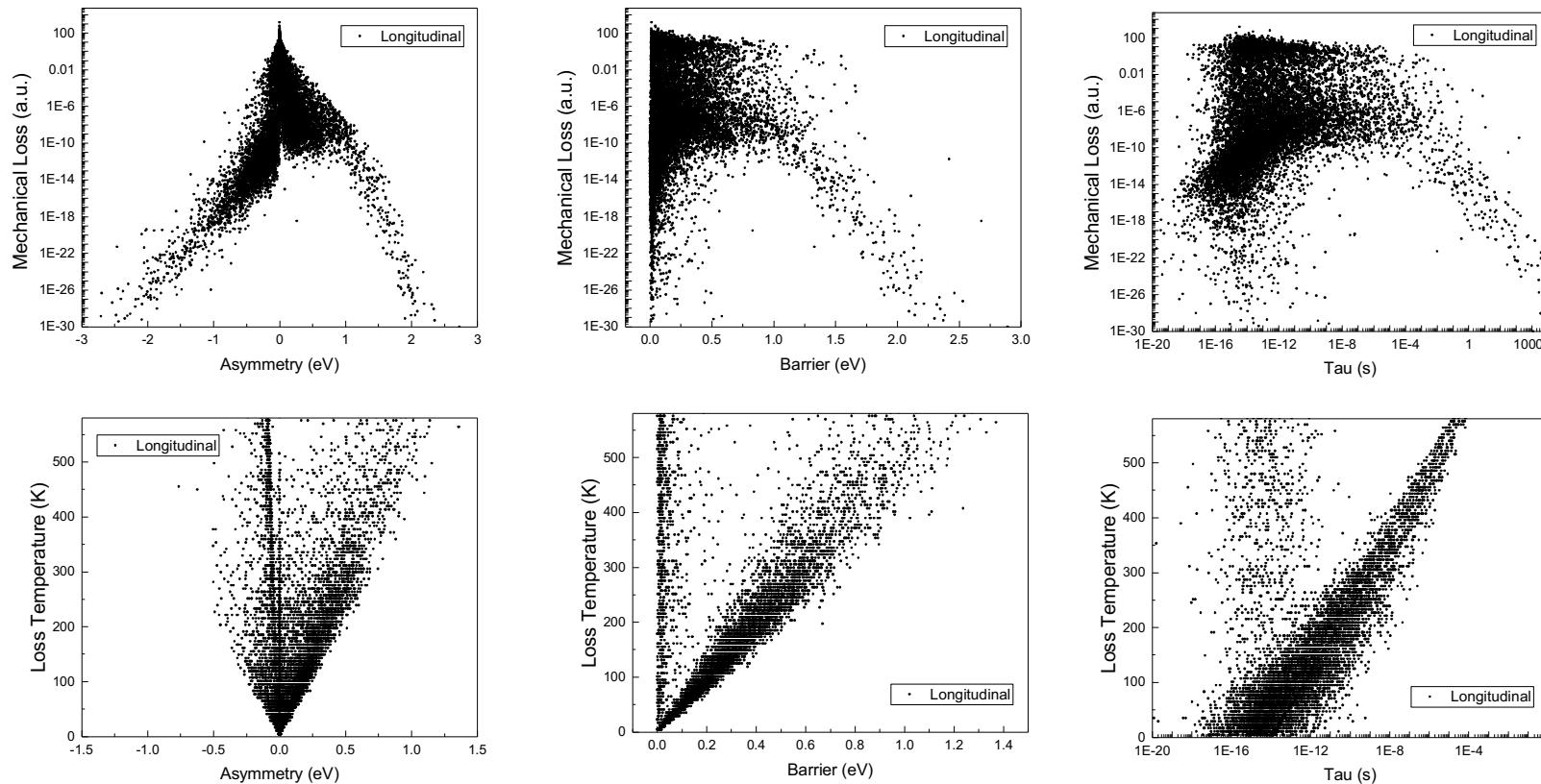


Saddle -> Minimum2

Large Asymmetry

Small Asymmetry

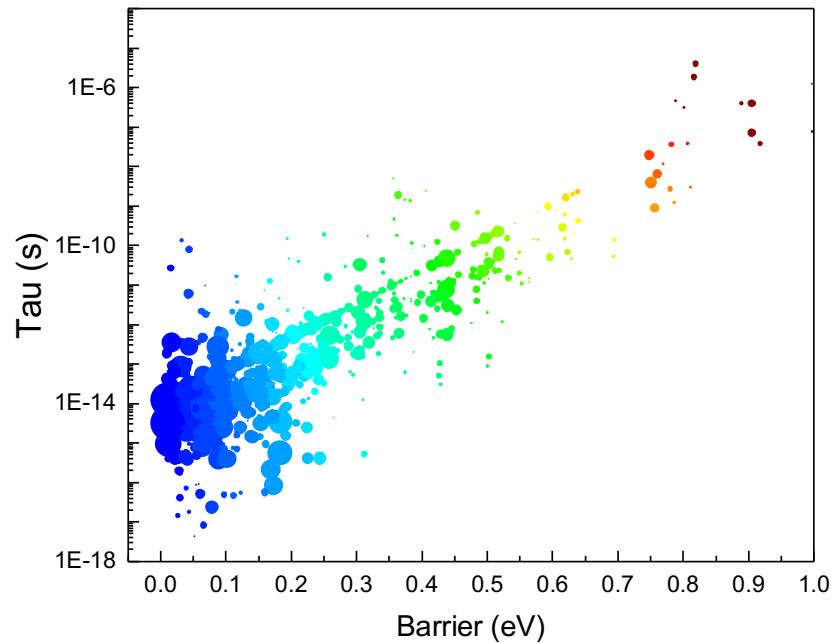
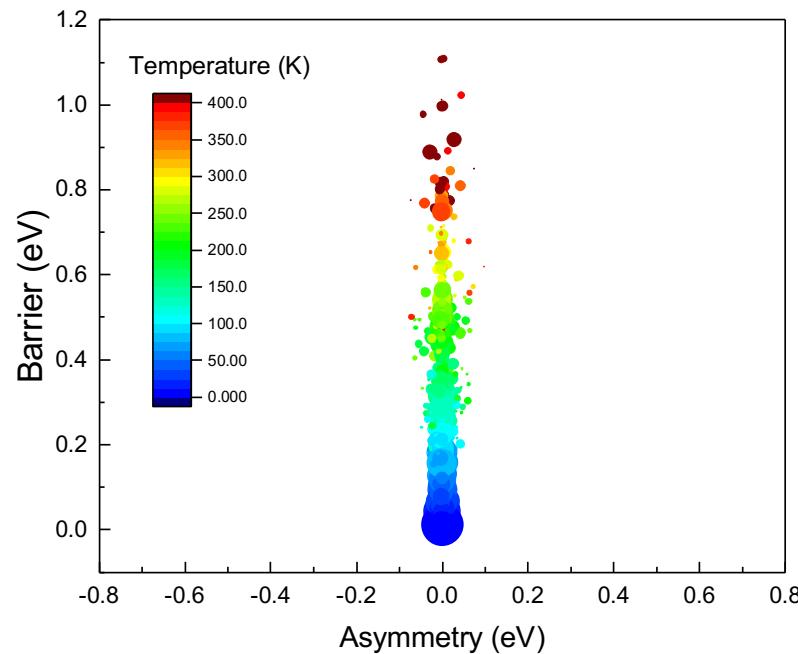
## Mechanical Loss vs Barrier ( Asymmetry, relaxation time )



Identify the relation between loss peak centers at different temperature with barrier, asymmetry and relaxation time.

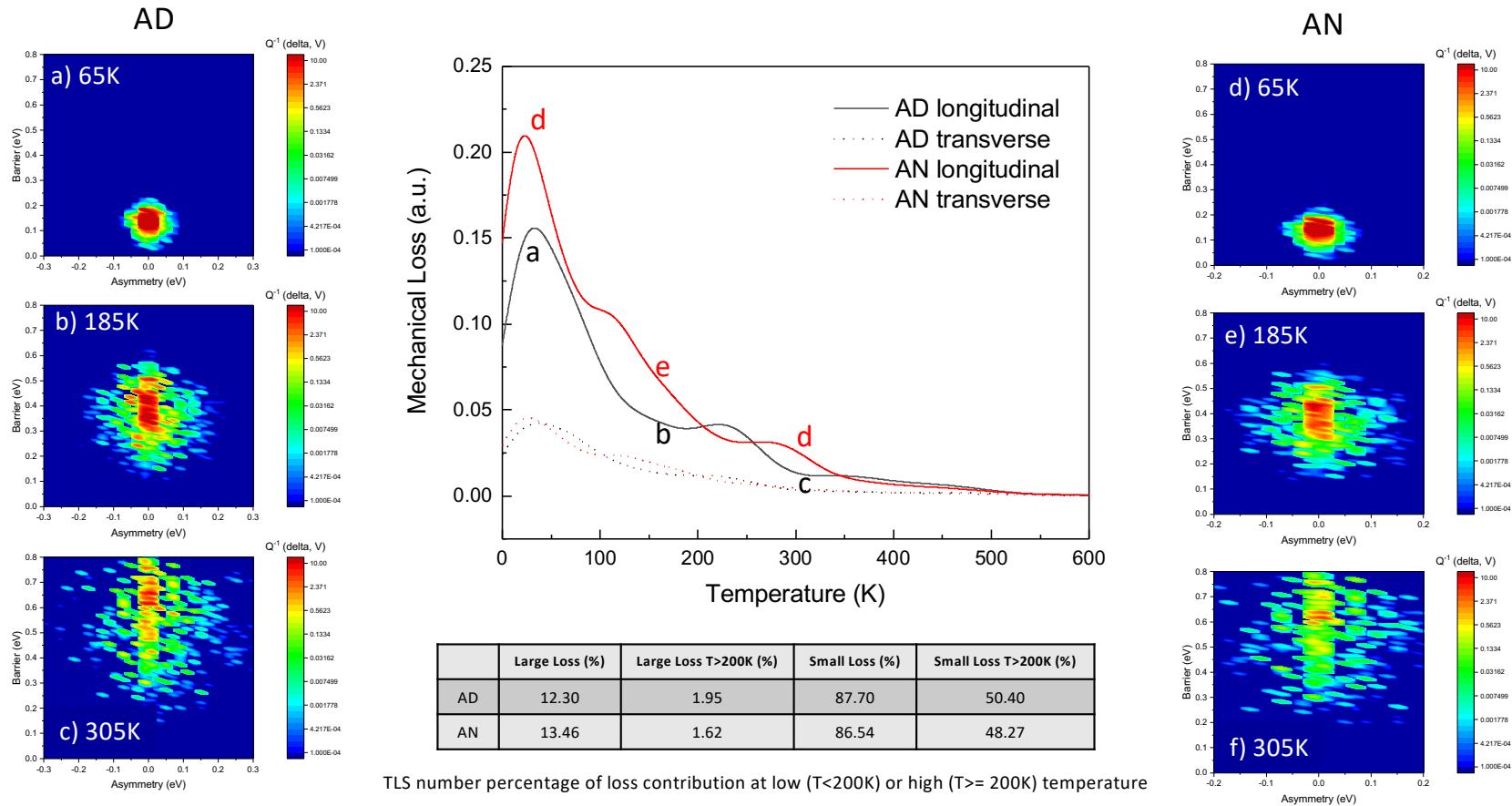
## TLSS that has large contribution to mechanical loss

Color: Temperature  
Size: Diameter  $\propto \text{Log(loss)}$



Low asymmetry gives main loss contribution; Higher barrier gives loss at higher temperature

## Mechanical Loss of 50% ZrO<sub>2</sub> doped Ta<sub>2</sub>O<sub>5</sub>



Calculated transverse loss is smaller than Longitudinal loss.

The AN models have larger mechanical loss compare to AD models, except the range about 240 K.

# Summary

- Main mechanical loss is contributed by low asymmetry TLS transition
- TLS transitions with higher barrier give loss at higher temperature
- Calculated mechanical loss for AN (800C annealed) is higher than AD (As-deposited)